

REMARKS

Claims 1-30 are pending, with claims 1, 2, 9, and 10 being independent. Claims 1, 2, 9, 10, and 17-20 have been examined and claims 3-8, 11-16, and 21-30 have been withdrawn from consideration due to a previous restriction requirement.

Claims 1, 2, 9, 10, and 17-20 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Applicants' Prior Art (APA) in view of Asano (5,409,867). Claims 1, 2, 9, and 10 have been amended to obviate this rejection.

As amended, claims 1, 2, 9, and 10 recite a method for manufacturing a semiconductor device having at least one thin film transistor that includes, among other steps, irradiating the semiconductor layer with a laser beam to crystallize a semiconductor layer, where the laser beam is a second harmonic component having a wavelength of 532 nm generated from a continuously-oscillating light source. Applicants respectfully request withdrawal of this rejection because APA and Asano, either alone in combination, fail to describe or suggest irradiating the semiconductor layer with a laser beam that is a second harmonic component having a wavelength of 532 nm generated from a continuously-oscillating light source.

As acknowledged in the Office Action, APA fails to describe or suggest a linear laser beam that is a second harmonic component generated from a continuously-oscillating light source. Asano does not remedy this failure of APA. The Office Action relies upon Asano for the notion that a continuous-wave type laser, such as, for example, the visible ray of wavelength 515 nm from an argon ion, may be used. However, Asano fails to describe or suggest using a second harmonic component having a wavelength of 532 nm as now recited in amended claims 1, 2, 9, and 10. Thus, because neither APA nor Asano describes or suggests using a laser beam that is a second harmonic component having a wavelength of 532 nm generated from the continuously-oscillating light source, a prima facie case of obviousness cannot be established.

Furthermore, amended claims 1 and 2 recite that the irradiation of the semiconductor layer is conducted in such a manner that the semiconductor layer is scanned with the linear laser beam in parallel with a carrier flow direction in the channel region. As acknowledged in the Office Action, APA does not describe or suggest that the semiconductor layer is scanned with

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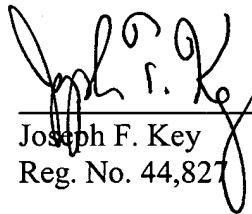
the linear laser beam in parallel with a carrier flow direction in the channel region. Asano does not remedy this failure of APA. Although Asano teaches that crystallizing an amorphous semiconductor layer by irradiating a laser light while a substrate is moved, Asano fails to describe or suggest any relationship between the scanning direction of the laser light and a carrier flow direction as recited in amended claims 1 and 2.

For at least these reasons, Applicants respectfully request the withdrawal of § 103(a) rejection of claims 1, 2, 9, and 10, and their dependent claims 17-20.

Enclosed is a \$110.00 check for the Petition for Extension of Time fee. During prosecution of this case, please apply any deficiencies or credits to deposit account 06-1050.

Respectfully submitted,

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